

WS7802C

0.1GHz - 3GHz SPDT Antenna Switch

Descriptions

The WS7802C is a Single Pole, Double-Throw (SPDT) switch. The device is optimized for 4G routing and diversity applications. The high linearity performance and low insertion loss make the device an ideal choice for WCDMA/LTE handset and data card applications. The WS7802C is provided in a compact Land Grid Array (LGA) 1.1 x 0.7 mm² package.

Features

- Small, low profile package 1.1mm x 0.7mm x 0.45mm
- Working frequency up to 3GHz
- · Very low insertion loss
- Excellent isolation performance
- Low power consumption
- Exceptional linearity performance for WCDMA/LTE application
- · Low harmonic generation
- Very good ESD performance

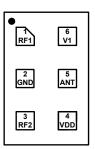
Applications

- Cell phones
- Tablets
- Other RF front-end modules

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LGA 1.1X0.7-6L (Bottom view)



Pin configuration (Top view)



Z = Device code

* = Month code (A~Z)

Marking(Top view)

Order information

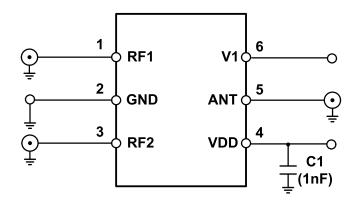
Device	Package	Shipping	
WS7802C-6/TR	LGA 1.1X0.7-6L	6000/Reel&Tape	



Pinning information

Pin	Function	Description	Transparent top view		
1	RF1	RF port 1	•		
2	GND	Ground	6 RF1 01		
3	RF2	RF port 2	2 5		
4	VDD	DC power supply	GND ANT		
5	ANT	RF common (antenna) port	3 4 RF2 VDD		
6	V1	DC control voltage1			

Application information



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Recommended operating conditions

Parameters	Conditions	Specifications			Unit
		Min.	Тур.	Max.	
ESD Rating					
ESD All Pins	HBM, JESD22-A114			1000	V
Power Supply					
Power Supply Voltage	Operating Voltage	2.4	2.8	3.0	V
Power Supply Current	VDD≤3.0V	20	28	40	μA
Control Voltage					
Logic Control "Low"		0	0	0.3	V
Logic Control "High"		1.2	1.8	2.7	V
RF Impedance					
RF Port Input and Output Impedance			50		Ω

Absolute maximum ratings

Maximum ratings are absolute ratings, exceeding only one of these values may cause irreversible damage to the integrated circuit.

Items	Value	Unit
VDD Voltage	-0.3 to +3.0	٧
Control Voltage	-0.3 to +2.7	V
Maximum Input Power @ RF ports	26@0.88GHz, 32@2.0GHz	dBm
Operation Temperature	-40 to +85	°C
Storage Temperature	-65 to +150	°C

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Characteristics (RF spec)

Normal test condition unless other-wise stated. All unused ports are 50Ω terminated. VDD=2.8V, Temp=+25°C. P_{IN} =0dBm.

Parameters	Conditions	Spe	Specifications			
		Min.	Тур.	Max.		
Incoming Loop	0.1GHz to 1.0GHz		0.40	0.55		
Insertion Loss	1.0GHz to 2.0GHz		0.45	0.60	dB	
(RF1/RF2)	2.0GHz to 2.7GHz		0.50	0.65		
la alakia a	0.1GHz to 1.0GHz	32				
Isolation	1.0GHz to 2.0GHz	28			dB	
(ANT to RF1/RF2)	2.0GHz to 2.7GHz	24				
Return Loss	0.1GHz to 1.0GHz	25				
	1.0GHz to 2.0GHz	22			dB	
(ANT/RF1/RF2)	2.0GHz to 2.7GHz	20				
Second Harmonics (RF1/RF2)	P _{IN} =+26dBm@0.88G		84		dBc	
Third Harmonics (RF1/RF2)	P _{IN} =+26dBm@0.88G		78		dBc	
0.1dB Compression Point	@0.88GHz		24		dDm	
(RF1/RF2)	@2.00GHz		30		dBm	
3 rd Order Input Intercept Point	P ₂ = +20dBm,					
(RF1/RF2)	P ₁ = -15dBm,		55		dBm	
(141 1/141 2)	Note 1					

Note 1: f_2 =836.5MHz, f_1 =791.5MHz, f_{IMD3} =881.5MHz

Truth Table for Operation

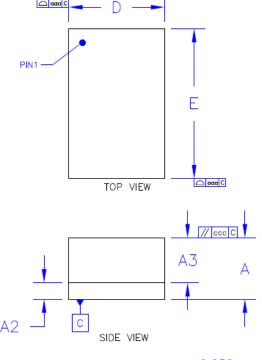
Mode	V1
RF1	1
RF2	0

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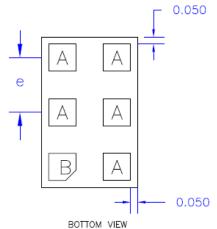


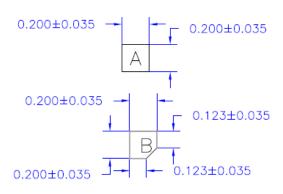
Package outline dimensions

LGA 1.1X0.7-6L



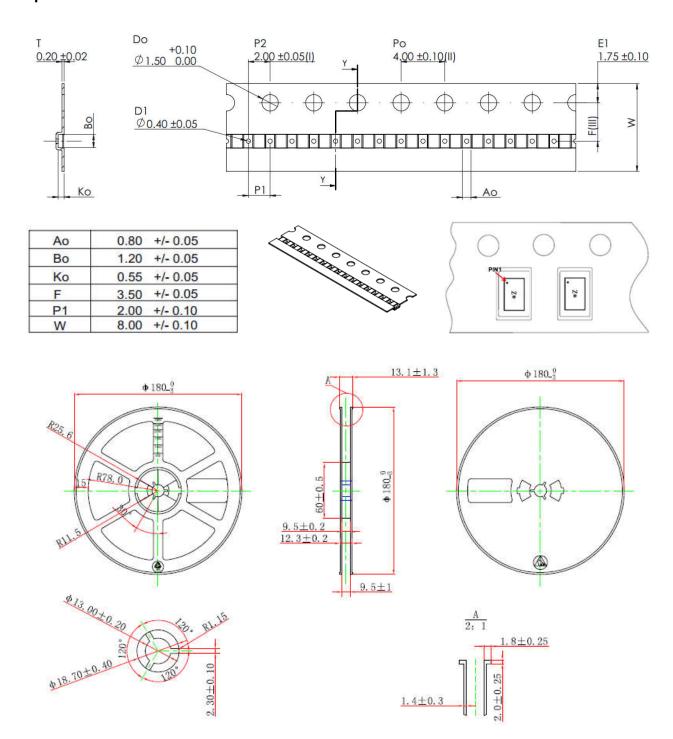
MILLIMETER				
SYMBOL	MIN	NOR	MAX	
Α	_	0.45	0.53	
A2	0.09	0.12	0.15	
A3	0.28	0.33	0.38	
е	0.35	0.40	0.45	
D	0.65	0.70	0.75	
Ε	1.05	1.10	1.15	
aaa	0.10			
ccc	0.20			







Tape reel information



Note:

- 1. Measured from centreline of sprocket hole to centreline of pocket.
- 2. Cumulative tolerance of 10 sprocket holes is \pm 0.20.
- 3. Measured from centreline of sprocket hole to centreline of pocket.
- 4. All dimensions in millimetres unless otherwise stated.

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